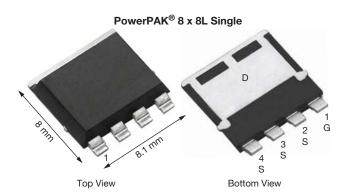
www.vishay.com

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



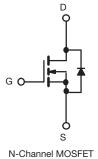
PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0012
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0015
I _D (A)	200
Configuration	Single
Package	PowerPAK 8 x 8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



FREE



ABSOLUTE MAXIMUM RATINGS (T	_C = 25 °C, unles	s otherwise noted	l)		
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V _{DS}	40	v		
Gate-source voltage	V _{GS}	V _{GS} ± 20			
Continuous drain current	T _C = 25 °C ª	1	200		
Continuous drain current	T _C = 125 °C	I _D	141		
Continuous source current (diode conduction)		ا _S	136	А	
Pulsed drain current ^b		I _{DM}	600		
Single pulse avalanche current		I _{AS}	50		
Single pulse avalanche energy	L = 0.1 mm	E _{AS}	125	mJ	
Maximum newer discinction	T _C = 25 °C	D	150	W	
Maximum power dissipation	T _C = 125 °C	P _D	50		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATINGS PARAMETER SYMBOL LIMIT UNIT Junction-to-ambient PCB mount ^c R_{thJA} 50 °C/W 1 Junction-to-case (drain) R_{thJC}

Notes

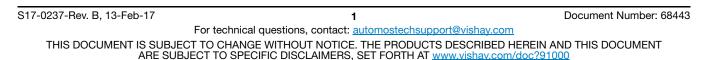
a. Package limited

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

c. When mounted on 1" square PCB (FR4 material)

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components





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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static		•						
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		40	-	-	v	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2	2.5	v	
Gate-source leakage	I _{GSS}	V _{DS} =	= 0 V, V_{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS}=40~V,~T_J=125~^\circ C$	-	-	50	μA	
ate-source leakage ero gate voltage drain current n-state drain current ^a rain-source on-state resistance ^a prward transconductance ^b ynamic ^b put capacitance utput capacitance everse transfer capacitance otal gate charge ^c ate-source charge ^c		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	500	1	
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	100	-	-	А	
Drain-source on-state resistance ^a		$V_{GS} = 10 \text{ V}$	I _D = 20 A	-	0.0009	0.0012		
	В	$V_{GS} = 4.5 V$	I _D = 10 A	-	0.0011	0.0015	Ω	
	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 20 A, T _J = 125 °C	-	-	0.0018		
		$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	0.0022					
Forward transconductance b	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 15 \text{ A}$		-	122	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	10 810	14 500		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	6500	8500	pF	
Reverse transfer capacitance	C _{rss}			-	700	950		
Total gate charge ^c	Qg		$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	140	220	nC	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 V$		-	30	-		
Gate-drain charge ^c	Q _{gd}			-	20	-		
Gate resistance	Rg	f = 1 MHz		0.45	0.99	1.50	Ω	
Turn-on delay time ^c	t _{d(on)}			-	24	40		
Rise time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 2 \Omega$ $I_{D} \cong 10 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	60	100	- ns	
Turn-off delay time ^c	t _{d(off)}			-	60	100		
Fall time ^c	t _f			-	30	50		
Source-Drain Diode Ratings and Cha	aracteristics ^b							
Pulsed current ^a	I _{SM}			-	-	200	Α	
Forward voltage	V _{SD}	le :	= 50 A, V _{GS} = 0	-	0.8	1.2	V	

Notes

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

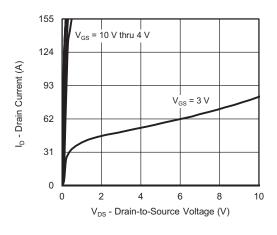
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

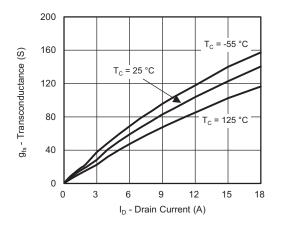


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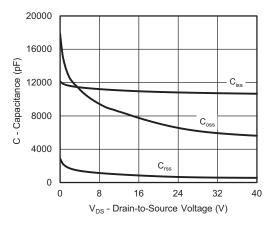
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



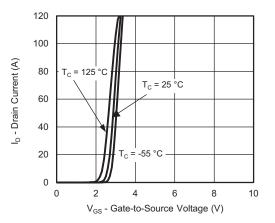
Output Characteristics



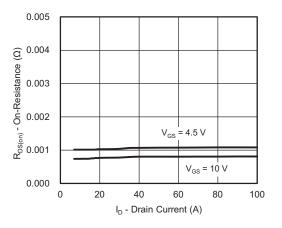
Transconductance



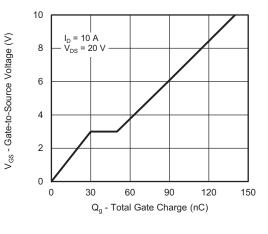
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

S17-0237-Rev. B, 13-Feb-17

3

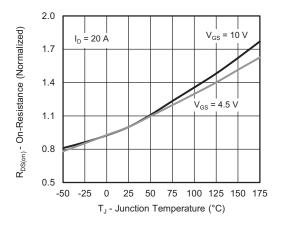
Document Number: 68443

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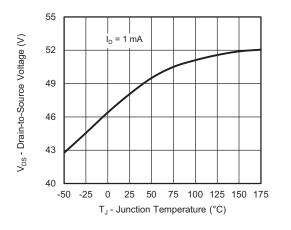


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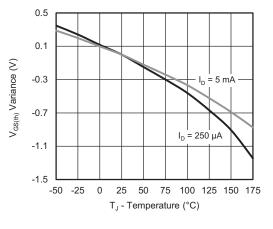
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



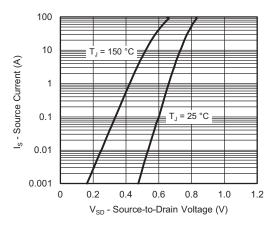
On-Resistance vs. Junction Temperature



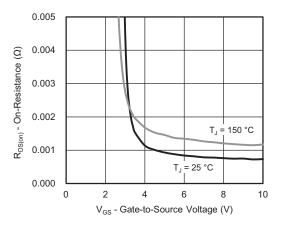
Drain Source Breakdown vs. Junction Temperature



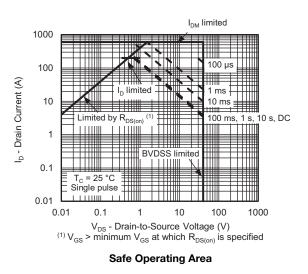
Threshold Voltage



Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



S17-0237-Rev. B, 13-Feb-17

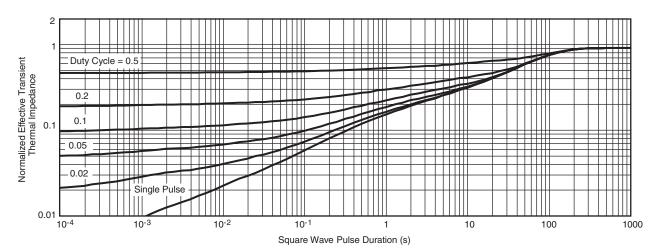
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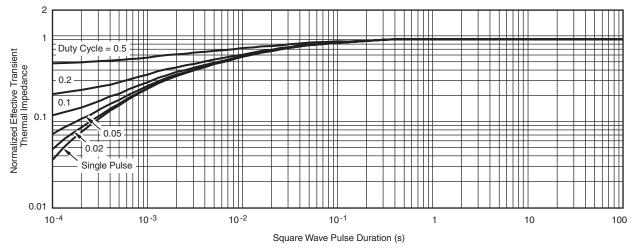


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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



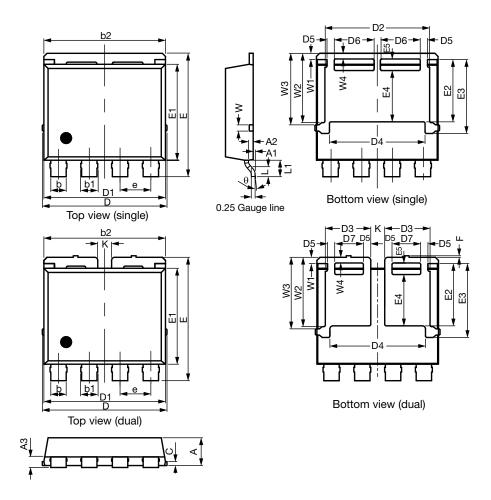
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68443.



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DIM.		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.70	1.80	1.90	0.067	0.071	0.075	
A1	0.00	0.08	0.13	0.000	0.003	0.005	
A2	0.25	0.30	0.35	0.010	0.012	0.014	
A3	0.55	0.62	0.70	0.022	0.024	0.028	
b	0.92	1.00	1.08	0.036	0.039	0.043	
b1	1.02	1.10	1.18	0.040	0.043	0.046	
b2	7.80	7.90	8.00	0.307	0.311	0.315	
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	8.00	8.10	8.25	0.315	0.319	0.325	
D1	7.80	7.90	8.00	0.307	0.311	0.315	
D2	6.70	6.80	6.90	0.264	0.268	0.272	
D3	2.85	2.95	3.05	0.112	0.116	0.120	
D4	6.11	6.21	6.31	0.241	0.244	0.248	
D5	0.37	0.47	0.57	0.015	0.019	0.022	
D6	2.49	2.59	2.69	0.098	0.102	0.106	
D7	1.76	1.86	1.96	0.069	0.073	0.077	

Revision: 16-Oct-17

Document Number: 67734

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Package Information





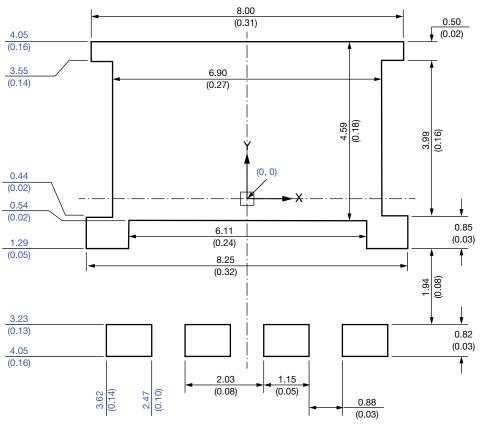
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DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
Е	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	



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Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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